EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1595	(257/e21.228).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/12 10:43
L2	452	(438/775).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/12 10:43
L3	142	(438/776).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/12 10:43
L4	1156	(438/770).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/12 10:43
S1	107	nitric acid with "80" degrees	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/25 15:12
S2	17	nitric acid with "80" degrees and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/25 15:12
S3	305	heated with nitric acid and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/25 15:12

S4	0	heated with nitric acid with defect with removal and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/30 00:53
S5	1	heated with nitric acid with defect and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/30 00:55
S6	305	heated with nitric acid and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/30 00:55
S7	31	heated with nitric acid with oxide and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/30 00:57
S8	13	heated with nitric acid with known and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/30 01:00
S9	22	heat$3 with nitric acid with known and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/30 10:02
S10	0	heat$3 with nitric acid with known withoxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/30 10:03
S11	25	heat$3 with nitric acid with known with oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/30 10:03

S12	0	nitric acid with "80" degrees with known	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/30 10:07
S13	34	nitric acid with degrees with known	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/25 15:14
S14	6	nitric acid with degrees with known and silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/30 10:15
S15	0	heated near nitric acid with known and silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/30 10:16
S16	33	heated near nitric acid and silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/30 10:35
S17	198	"hno.sub.3" and "80" degrees	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/25 15:12
S18	13	"hno.sub.3" with "80" degrees	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/30 10:36
S19	2	("6117689").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/31 14:28

S20	5	("2005013689").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/31 14:29
S21	2	("20050013689").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/31 14:30
S22	1	("20050136689").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/31 14:30
S23	206	"hno.sub.3" and "80" degrees	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/25 15:12
S24	107	nitric acid with "80" degrees	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/25 15:12
S25	17	nitric acid with "80" degrees and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/25 15:12
S26	310	heated with nitric acid and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/08/06 07:24
S27	3923	(438/694).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/06 07:24

S28	414	(438/695).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/06 07:25
S29	1314	(438/745).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/06 07:25
S30	371	(438/775).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/06 07:25
S31	120	(438/776).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/06 07:25
S32	1033	(438/770).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/06 07:25
S33	34	nitric acid with degrees with known	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/25 15:14
S34	278	NAKAMURA-MANABU.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/08/06 07:25
S35	13	NANSEI-HIROYUKI.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/08/06 07:26

S36	12	SERA-KENTARO.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/08/06 07:26
S37	25	HIGASHI-MASAHIKO .in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/08/06 07:26
S38	10	UTSUNO-YUKIHIRO .in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/25 15:16
S39	185	TAKAGI-HIDEO.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/08/06 07:26
S40	63	KAJITA-TATSUYA .in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/08/06 07:26
S41	74	(257/e21.221).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/25 15:21
S42	4	tunnel oxide with plasma oxidation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/02/07 12:27
S43	3	nitric acid and tunnel oxide and plasma with oxidation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/02/07 12:29

S44	335	nitric acid with clean$3 same semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/02/07 12:30
S45	1	nitric acid with clean$3 same semiconductor and tunnel oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/02/07 12:31
S46	108	nitric acid with clean$3 same semiconductor same oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/02/07 12:33
S47	7	nitric acid with clean$3 same semiconductor same oxide and plasma with oxid$6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/08/06 07:27
S48	16	"5423944"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/02/07 12:42
S49	518	acid with ozone and plasma with oxidation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/02/26 13:14
S50	18	acid with ozone and plasma with oxidation and insulation film	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/02/26 18:24
S51	2	("5423944").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/02/26 18:29

S52	117	nitric acid with ozone same silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/02/26 18:30
S53	25	nitric acid with ozone same silicon same temperature	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/02/26 18:31
S54	2	("5412216").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/02/26 20:05
S55	2	("5412246").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/02/26 20:05
S56	2	("5423944").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/06 06:55
S57	2	("5412246").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/06 06:54
S58	4054	(438/694).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/06 07:24
S59	347	heated with nitric acid and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/08/06 07:25

S60	455	(438/695).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/06 07:25
S61	1535	(438/745).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/06 07:25
S62	428	(438/775).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/06 07:25
S63	138	(438/776).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/06 07:25
S64	1118	(438/770).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/06 07:25
S65	308	NAKAMURA-MANABU.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/08/06 07:25
S66	20	NANSEI-HIROYUKI.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/08/06 07:26
S67	14	SERA-KENTARO.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/08/06 07:26

S68	38	HIGASHI-MASAHIKO .in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/08/06 07:26
S69	192	TAKAGI-HIDEO.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/08/06 07:26
S70	65	KAJITA-TATSUYA .in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/08/06 07:26
S71	8	nitric acid with clean$3 same semiconductor same oxide and plasma with oxid$6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/08/06 07:39
S72	1569	(257/e21.228).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/06 07:39
S73	193	radial line slot antenna with plasma with microwave	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/02/27 21:18
S74	7	radial line slot antenna with plasma with microwave same insulation film	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/02/27 21:18
S76	68	(radial line slot antenna or rlsa) with plasma same microwave and insulation film	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/02/27 21:25

S77	7	(radial line slot antenna or rlsa) with plasma same microwave same insulation film	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/01 17:19

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